

## Silicon PNP transistor epitaxial type AP884

### [ Applications ]

High voltage switching and amplifier

### [ Feature ]

High voltage  $V_{CEO} = -500V$

Excellent hFE characteristics up to  $I_C = -150mA$

Low collector saturation voltage  $V_{CE(sat)} = -0.5V$  (Max.) at  $I_C = -50mA$ ,  $I_B = -10mA$

### [ Absolute maximum ratings (Ta=25C) ]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-500	V
Collector-emitter voltage	VCEO	-500	V
Emitter-base voltage	VEBO	-5	V
Collector current	IC	-150	mA
Collector current (pulse)	ICP	-500	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

### [ Electrical characteristics (Ta=25C) ]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-500	-	-	V	$I_C = -100\mu A$
Collector-emitter breakdown voltage	BVCEO	-500	-	-	V	$I_C = -10mA$
Emitter-base breakdown voltage	BVEBO	-5	-	-	V	$I_E = -100\mu A$
Collector cut-off current	ICBO	-	-	-100	nA	$V_{CB} = -500V$
Collector cut-off current	ICES	-	-	-100	nA	$V_{CES} = -500V$
Emitter cut-off current	IEBO	-	-	-100	nA	$V_{EB} = -5V$
DC current gain 1	hFE 1	150	-	300	-	$V_{CE} = -10V$ , $I_C = -1mA$
DC current gain 2	hFE 2	80	-	300	-	$V_{CE} = -10V$ , $I_C = -50mA$
DC current gain 3	hFE 3	-	15	-	-	$V_{CE} = -10V$ , $I_C = -100mA$
Collector-emitter saturation voltage 1	$V_{CE(sat)1}$	-	-	-0.2	V	$I_C = -20mA$ , $I_B = -2mA$
Collector-emitter saturation voltage 2	$V_{CE(sat)2}$	-	-	-0.5	V	$I_C = -50mA$ , $I_B = -10mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	-	-	-0.9	V	$I_C = -50mA$ , $I_B = -10mA$
Base-emitter on voltage	$V_{BE(on)}$	-	-	-0.9	V	$V_{CE} = -10V$ , $I_C = -50mA$
Transition frequency	fT	50	-	-	MHz	$V_{CE} = -20V$ , $I_E = 10mA$
Collector output capacitance	Cob	-	-	8	pF	$V_{CB} = -20V$ , $f = 1MHz$ , $I_E = 0A$
Turn on time	ton	-	110	-	ns	$V_{CE} = -100V$ , $I_C = -50mA$
Turn off time	toff	-	1500	-	ns	$I_{B1} = -5mA$ , $I_{B2} = 10mA$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 IC - VBE(on)  
at VCE = -10V, Ta = 25C

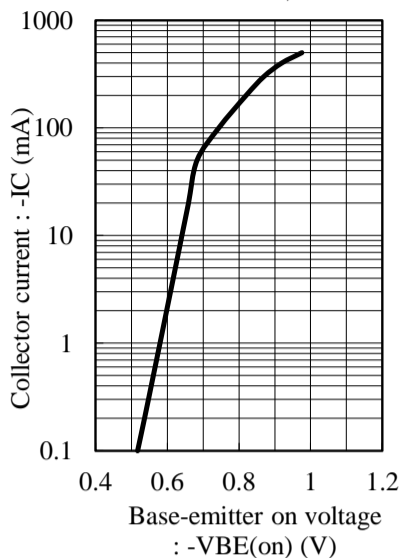


Fig.2 hFE - IC  
at VCE = -5V, Ta = 25C

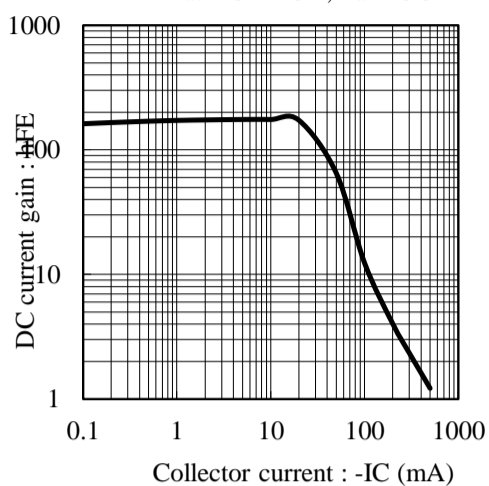


Fig.3 hFE - IC  
at VCE = -10V, Ta = 25C

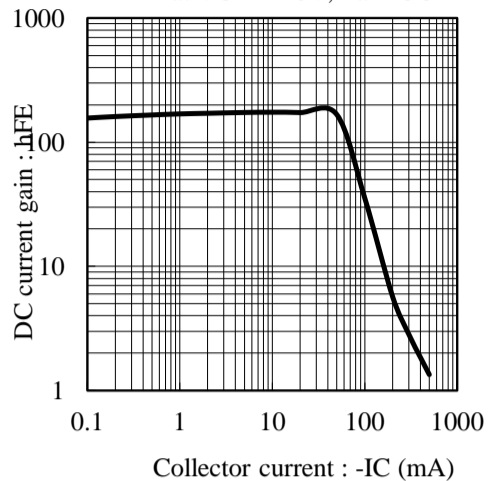


Fig.4 VCE(sat) - IC  
at IC/IB = 5, Ta = 25C

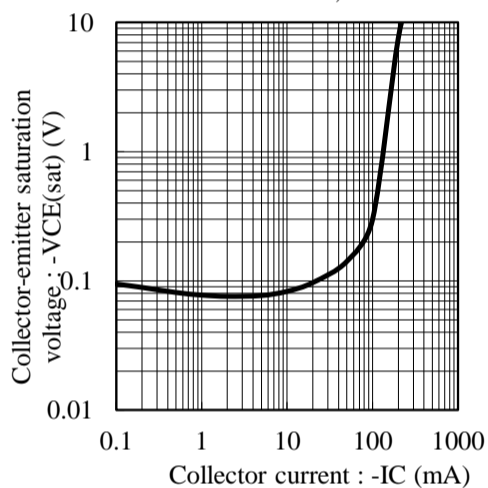


Fig.5 VCE(sat) - IC  
at IC/IB = 10, Ta = 25C

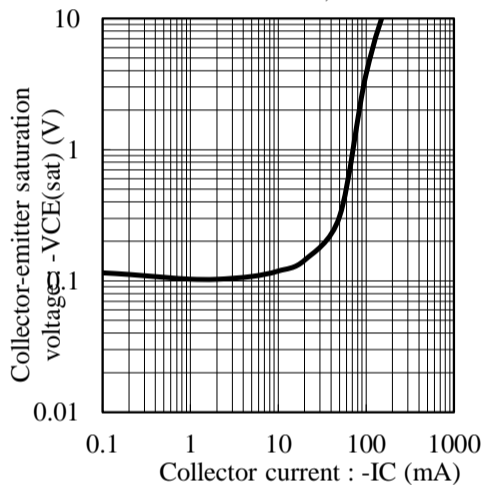


Fig.6 VBE(sat) - IC  
at IC/IB = 5, Ta = 25C

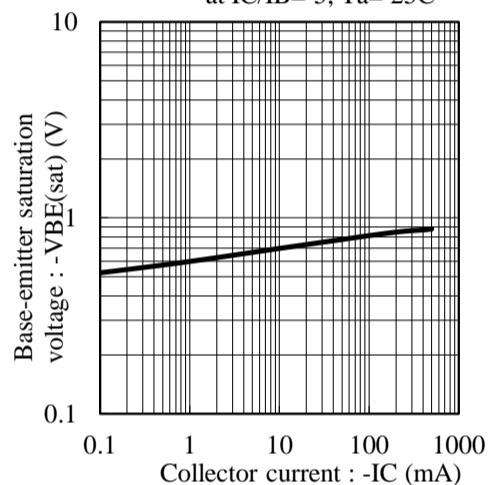


Fig.7 VBE(sat) - IC  
at IC/IB = 10, Ta = 25C

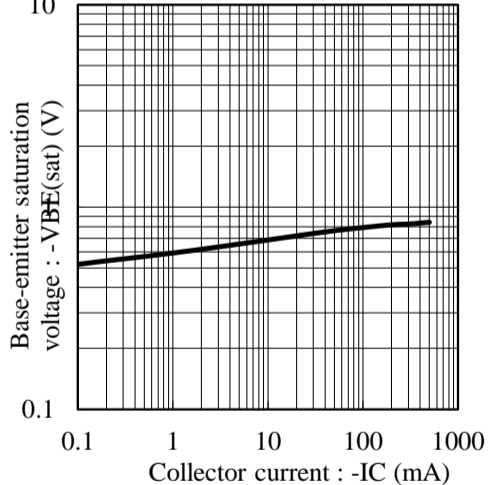


Fig.8 fT - IE  
at VCE = -20V, Ta = 25C

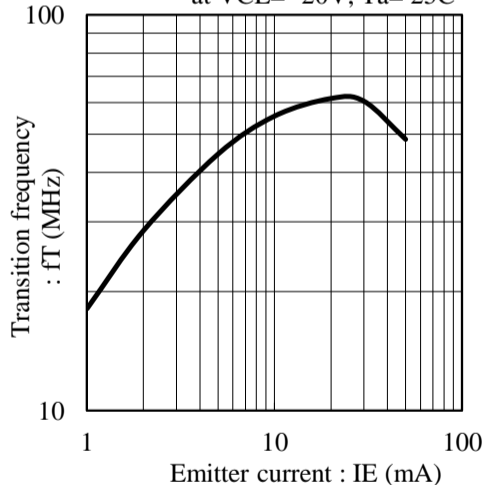


Fig.9 Cob - VCB  
at f = 1MHz, Ta = 25C

